

TECHNICAL DATA  
DATA SHEET 5067, REV. -

**FAST RECOVERY  
SILICON RECTIFIER DIE**

**Maximum Ratings:**

Characteristics	Symbol	Condition		Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	1C5415 1C5416 1C5417 1C5418 1C5419 1C5420	50 100 200 400 500 600	V (pk)
Max. Average Forward Current	$I_{F(AV)}$	@ 55°C		3.0	A dc
Max. Junction Temperature	$T_J$	-		-55 to +175	°C
Max. Storage Temperature	$T_{stg}$	-		-55 to +175	°C

**Electrical Characteristics:**

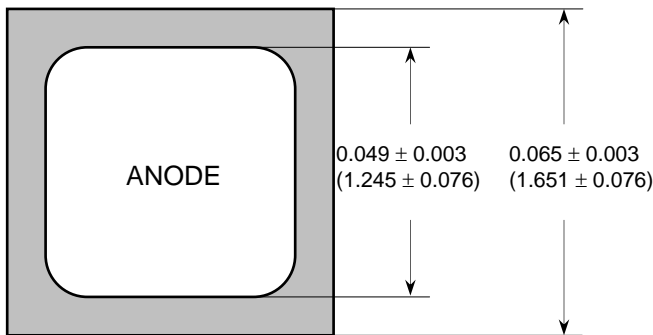
Characteristics	Symbol	Condition		Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	$I_F=1.5A$		1.2	V dc
	$V_{F2}$	$I_F=9.0A$ dc, Pulse, $T_J = 25\text{ °C}$ , Duty cycle $\leq 2\%$ , pulse width $\leq 300\mu s$		1.5	V (pk)
Max. Reverse Current	$I_{R1}$	@ $V_R = V_{RWM}$ , Pulse, $T_J = 25\text{ °C}$		1.0	$\mu A$ dc
	$I_{R2}$	@ $V_R = V_{RWM}$ , Pulse, $T_J = 100\text{ °C}$		20	$\mu A$ dc
Reverse Recovery Time	$t_{rr}$	$I_f = 500mA$ , $I_r = 1A$ , $I_{rm} = 250mA$	1C5415 1C5416 1C5417 1C5418 1C5419 1C5420	150 150 150 150 250 400	ns

**SENSITRON**  
**SEMICONDUCTOR**

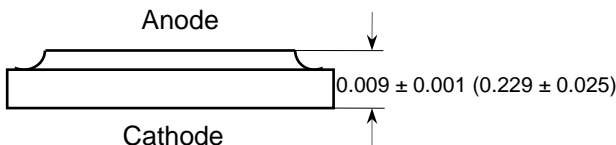
1C5415  
1C5416  
1C5417  
1C5418  
1C5419  
1C5420

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**Mechanical Dimensions: In Inches / mm**



Top side metalization - Aluminum - 25 kÅ minimum.  
Bottom side metalization - Ti/Ni/Ag - 30 kÅ minimum  
Bottom side is cathode, top side is anode.



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